

MICROWAVE POWER GAAS FET

TIM1414-4LA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- **·BROAD BAND INTERNALLY MATCHED FET**
- ·HIGH POWER

P1dB= 36.5dBm at 14.0GHz to 14.5GHz

·HIGH GAIN

G1dB= 6.5dB at 14.0GHz to 14.5GHz

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V IDSset= 2.0A f= 14.0 to 14.5GHz	dBm	36.0	36.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.0	6.5	_
Drain Current	IDS1		Α	_	1.7	2.2
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%	_	23	_
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 24.0dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	_
Drain Current	IDS2		Α	_	1.7	2.2
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_	_	60

Recommended Gate Resistance(Rg): 150 Ω

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.0A	S	_	1.2	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 60mA	V	-2.0	-3.5	-5.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	4.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -60μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	2.9	3.5

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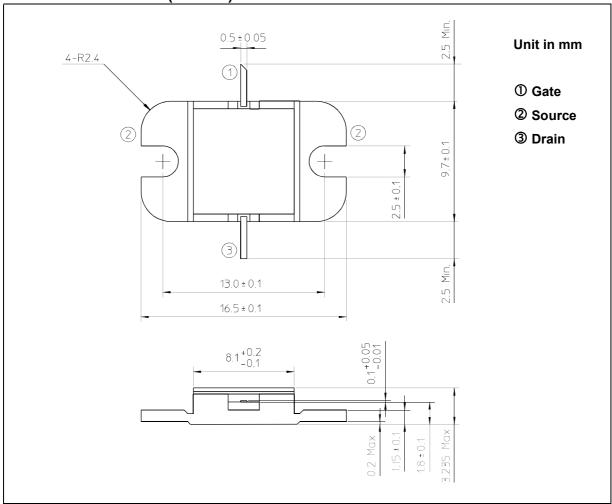


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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	5.2
Total Power Dissipation (Tc= 25°C)	PT	W	42.8
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

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